

TC1121

100mA Charge Pump Voltage Converter with Shutdown

FEATURES

- Optional High-Frequency Operation Allows Use of Small Capacitors
- Low Operating Current (FC = GND) 50µA
- High Output Current 100mA
- Converts a 2.4V to 5.5V Input Voltage to a Corresponding Negative Output Voltage (Inverter Mode)
- Uses Only 2 Capacitors; No Inductors Required!
 Selectable Oscillator
- Frequency10kHz to 200kHz
- Power-Saving Shutdown Input
- Small Packages8-Pin MSOP,

8-Pin PDIP,

8-Pin SOIC

APPLICATIONS

- Laptop Computers
- Medical Instruments
- Disk Drives
- µP-Based Controllers
- Process Instrumentation

ORDERING INFORMATION

| Part No. | Package | Temp. Range |
|-----------|------------|-----------------|
| TC1121COA | 8-Pin SOIC | 0°C to +70°C |
| TC1121CPA | 8-Pin PDIP | 0°C to +70°C |
| TC1121CUA | 8-Pin MSOP | 0°C to +70°C |
| TC1121EOA | 8-Pin SOIC | – 40°C to +85°C |
| TC1121EPA | 8-Pin PDIP | – 40°C to +85°C |
| TC1121EUA | 8-Pin MSOP | – 40°C to +85°C |

FUNCTIONAL BLOCK DIAGRAM

GENERAL DESCRIPTION

The TC1121 is a charge pump converter with 100mA output current capability. It converts a 2.4V to 5.5V input to a corresponding negative output voltage. As with all charge pump converters, the TC1121 uses no inductors saving cost, size, and EMI.

An on-board oscillator operates at a typical frequency of 10kHz (at V⁺ = 5V) when the frequency control input (FC) is connected to ground. The oscillator frequency increases to 200kHz when FC is connected to V⁺, allowing the use of smaller capacitors. Operation at sub-10kHz frequencies results in lower quiescent current and is accomplished with the addition of an external capacitor from OSC (pin 7) to ground. The TC1121 also can be driven from an external clock connected OSC. Typical supply current at 10kHz is 50μ A, and falls to less than 1 μ A when the shutdown input is brought low, whether the internal or an external clock is used. The TC1121 is available in 8-pin SOIC, MSOP, and PDIP packages.

PIN CONFIGURATION





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ABSOLUTE MAXIMUM RATINGS*

| V _{DD} Supply Voltage | 6V |
|---|---------------------------------|
| Operating Temperature | |
| C Suffix | 0°C to 70°C |
| E Suffix | – 40°C to +85°C |
| OSC, FC, SHDN Input Voltage | 0.3V to (V ⁺ + 0.3V) |
| Output Short Circuit Duration | 10 Sec. |
| Storage Temperature | 65°C to +150°C |
| Power Dissipation ($T_A \le 70^{\circ}C$) | |
| PDIP | 730mW |
| SOIC | 470mW |
| MSOP | 333mW |
| Lead Temperature (Soldering, 10 sec) . | +300°C |

*Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS: $T_A = 0^{\circ}C$ to $70^{\circ}C$ (C suffix), $-40^{\circ}C$ to $+85^{\circ}$ (E suffix), $V^+ = 5V \pm 10\%$ C_{OSC} = OPEN, C1, C2 = 10μ F, FC = V⁺, SHDN = V_{IH}, unless otherwise specified. Typical values are at $T_A = 25^{\circ}C$.

| Symbol | Parameter | Test Conditions | Min | Тур | Max | Units |
|------------------|-------------------------------|---|-----------------------|------|-----|-------|
| I _{DD} | Active Supply Current | R _L = Open, FC = Open or GND | _ | 50 | 100 | μΑ |
| | | $R_L = Open, FC = V^+$ | — | 0.6 | 1 | mA |
| ISHUTDOWN | Shutdown Supply Current | $\overline{\text{SHDN}} = 0V$ | — | 0.2 | 1.0 | μA |
| V+ | Supply Voltage | | 2.4 | — | 5.5 | V |
| VIH | SHDN Logic High Input Voltage | | V _{DD} x 0.8 | — | _ | V |
| VIL | SHDN Logic Low Input Voltage | | _ | — | 0.4 | V |
| I _{IN} | Input Leakage Current | SHDN, OSC | - 1 | | 1 | μA |
| | | FC Pin | - 4 | — | 4 | |
| R _{OUT} | Output Source Resistance | I _{OUT} = 60 mA | — | 12 | 20 | Ω |
| lout | Output Current | V _{OUT} more negative than – 3.75V | 60 | 100 | — | mA |
| Fosc | Oscillator Frequency | Pin 7 Open, Pin 1 Open or GND | 5 | 10 | _ | kHz |
| | | $\overline{\text{SHDN}} = V_{\text{IH}}$, Pin 1 = V ⁺ | 100 | 200 | — | |
| P _{EFF} | Power Efficiency | FC = GND For All | | | | |
| | | $R_L = 2k$ between V ⁺ and V _{OUT} | 93 | 97 | _ | % |
| | | $R_L = 1 k\Omega$ between V_{OUT} and GND | 94 | 97 | — | |
| | | $I_L = 60 \text{ mA to GND}$ | <u> </u> | 92 | _ | |
| Veff | Voltage Conversion Efficiency | R _L = OPEN | 99 | 99.9 | | % |

| Pin No. (8-Pin MSOP, | Function | | |
|-------------------------|----------|--|--|
| PDIP, SOIC) | Symbol | Inverter | |
| 1 | FC | Frequency control for internal oscillator, FC = open, F_{OSC} = 10kHz typ; FC = V ⁺ , F_{OSC} = 200kHz typ,FC has no effect when OSC pin is driven externally. | |
| 2 | CAP+ | Charge-pump capacitor, positive terminal. | |
| 3 | GND | Power-supply ground input. | |
| 4 | CAP- | Charge-pump capacitor, negative terminal. | |
| 5 | OUT | Output, negative voltage. | |
| 6 | SHDN | Shutdown. | |
| 7 | OSC | Oscillator control input. An external capacitor can be added to slow the oscillator. Take care to minimize stray capacitance. An external oscillator also may be connected to overdrive OSC. | |
| 8 | V+ | Power-supply positive voltage input. | |

APPLICATIONS

Negative Voltage Converter

The TC1121 is typically used as a charge-pump voltage inverter. C1 and C2 are the only two external capacitors used in the operating circuit (see Figure 1).



Figure 1. Charge Pump Inverter

The TC1121 is not sensitive to load current changes, although its output is not actively regulated. A typical output source resistance of 11.8Ω means that an input of +5V results in - 5V output voltage under light load, and only decreases to - 3.8V typ with a 100mA load.

The supplied output current is from capacitor C2 during one-half the charge-pump cycle. This results in a peak-topeak ripple of: $V_{RIPPLE} = I_{OUT}/2(f_{PUMP})$ (C2) + I_{OUT} (ESR_{C2})

Where f_{PUMP} is 5kHz (one half the nominal 10kHz oscillator frequency), and C2 = 150µF with an ESR of 0.2 Ω , ripple is about 90mV with a 100mA load current. If C2 is raised to 390µF, the ripple drops to 45mV.

Changing Oscillator Frequency

The TC1121's clock frequency is controlled by four modes:

| FC | OSC | Oscillator Frequency |
|--------------------------------|--------------------|--|
| Open | Open | 10kHz |
| $FC = V^+$ | Open | 200kHz |
| Open or FC = V ⁺ | External Capacitor | See Typical Operating Characteristics |
| Open | External Clock | External Clock Frequency |

The oscillator runs at 10kHz (typical) when FC and OSC are not connected. The oscillator frequency is lowered by connecting a capacitor between OSC and GND, but FC can still multiply the frequency by 20 times in this mode.

An external clock source that swings within 100 mV of V⁺ and GND may overdrive OSC in the inverter mode. OSC can be driven by any CMOS logic output. When OSC is overdriven, FC has no effect.

Note that the frequency of the signal appearing at CAP⁺ and CAP⁻ is half that of the oscillator. In addition, by lowering the oscillator frequency, the effective output resistance of the charge-pump increases. To compensate for this, the value of the charge-pump capacitors may be increased.

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Because the 5kHz output ripple frequency may be low enough to interfere with other circuitry, the oscillator frequency can be increased with the use of the FC pin or an external oscillator. The output ripple frequency is half the selected oscillator frequency. Although the TC1121's quiescent current will increase if the clock frequency is increased, it allows smaller capacitance values to be used for C1 and C2.

Capacitor Selection

In addition to load current, the following factors affect the TC1121 output voltage drop from its ideal value 1) output resistance, 2) pump (C1) and reservoir (C2) capacitor ESRs, and 3) C1 and C2 capacitance.

The voltage drop is the load current times the output resistance. The loss in C2 is the load current times C2's ESR; C1's loss is larger because it handles currents greater than the load current during charge-pump operation. Therefore, the voltage drop due to C1 is about four times C1's ESR multiplied by the load current, and a low (or high) ESR capacitor has a greater impact on performance for C1 than for C2.

In general, as the TC1121's pump frequency increases, capacitance values needed to maintain comparable ripple and output resistance diminish proportionately.

Cascading Devices

To produce greater negative magnitudes of the initial supply voltage, the TC1121 may be cascaded (see Figure 3). Resulting output resistance is approximately equal to the sum of individual TC1121 R_{OUT} values. The output voltage (where n is an integer representing the number of devices cascaded) is defined by $V_{OUT} = -n (V_{IN})$.



Figure 3. Cascading TC1121s to Increase Output Voltage

Paralleling Devices

To reduce output resistance, multiple TC1121s may be paralleled (see Figure 4). Each device needs a pump capacitor C1, but the reservoir capacitor C2 serves all

FC VIN OSC TC1121 osc 7-0 osc CAP-TC1121 C1n GND C1 GND SHDN SHDN SHDN <*SHDN V_{ou}. C2 R_{OUT} = R_{OUT} (of TC1121)/n(number of devices) NOTES: *SHDN should be tied to VIN if not used

devices. The value of C2 should be increased by a factor of

n (the number of devices).

Figure 4. Paralleling TC1121s to Reduce Output Resistance

Combined Positive Supply Multiplication and Negative Voltage Conversion

Figure 5 shows this dual function circuit, in which capacitors C1 and C2 perform pump and reservoir functions to generate negative voltage. Capacitors C2 and C4 are the respective capacitors for multiplied positive voltage. This particular configuration leads to higher source impedances of the generated supplies due to the finite impedance of the common charge-pump driver.



Figure 5. Combined Positive Multiplier and Negative Converter

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PACKAGE DIMENSIONS



100mA Charge Pump Voltage Converter with Shutdown

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PACKAGE DIMENSIONS (Cont.)





WORLDWIDE SALES AND SERVICE

AMERICAS

Corporate Office 2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7200 Fax: 480-792-7277 Technical Support: 480-792-7627 Web Address: http://www.microchip.com

Rocky Mountain 2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7966 Fax: 480-792-7456

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Two Prestige Place, Suite 130 Miamisburg, OH 45342 Tel: 937-291-1654 Fax: 937-291-9175 **Detroit**

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New York

150 Motor Parkway, Suite 202 Hauppauge, NY 11788 Tel: 631-273-5305 Fax: 631-273-5335

San Jose Microchip Technology Inc. 2107 North First Street, Suite 590 San Jose, CA 95131 Tel: 408-436-7950 Fax: 408-436-7955 **Toronto** 6285 Northam Drive, Suite 108 Mississauga, Ontario L4V 1X5, Canada

Tel: 905-673-0699 Fax: 905-673-6509

ASIA/PACIFIC

China - Beijing Microchip Technology Beijing Office Unit 915 New China Hong Kong Manhattan Bldg. No. 6 Chaoyangmen Beidajie Beijing, 100027, No. China Tel: 86-10-85282100 Fax: 86-10-85282104 China - Shanghai Microchip Technology Shanghai Office Room 701, Bldg. B Far East International Plaza No. 317 Xian Xia Road Shanghai, 200051

Tel: 86-21-6275-5700 Fax: 86-21-6275-5060 Hong Kong

Microchip Asia Pacific RM 2101, Tower 2, Metroplaza 223 Hing Fong Road Kwai Fong, N.T., Hong Kong Tel: 852-2401-1200 Fax: 852-2401-3431

India

Microchip Technology Inc. India Liaison Office Divyasree Chambers 1 Floor, Wing A (A3/A4) No. 11, OíShaugnessey Road Bangalore, 560 025, India Tel: 91-80-2290061 Fax: 91-80-2290062 **Japan** Microchip Technology Intl. Inc. Benex S-1 6F

Benex S-1 6F 3-18-20, Shinyokohama Kohoku-Ku, Yokohama-shi Kanagawa, 222-0033, Japan Tel: 81-45-471- 6166 Fax: 81-45-471-6122 **Korea**

Microchip Technology Korea 168-1, Youngbo Bldg. 3 Floor Samsung-Dong, Kangnam-Ku Seoul, Korea Tel: 82-2-554-7200 Fax: 82-2-558-5934

ASIA/PACIFIC (continued)

Singapore Microchip Technology Singapore Pte Ltd. 200 Middle Road #07-02 Prime Centre Singapore, 188980 Tel: 65-334-8870 Fax: 65-334-8850 **Taiwan** Microchip Technology Taiwan 11F-3, No. 207 Tung Hua North Road Taipei, 105, Taiwan

Tel: 886-2-2717-7175 Fax: 886-2-2545-0139

EUROPE

Australia Microchip Technology Australia Pty Ltd Suite 22, 41 Rawson Street Epping 2121, NSW Australia Tel: 61-2-9868-6733 Fax: 61-2-9868-6755 Denmark Microchip Technology Denmark ApS Regus Business Centre Lautrup hoj 1-3 Ballerup DK-2750 Denmark Tel: 45 4420 9895 Fax: 45 4420 9910 France Arizona Microchip Technology SARL Parc díActivite du Moulin de Massv 43 Rue du Saule Trapu Batiment A - ler Etage 91300 Massy, France Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79 Germany Arizona Microchip Technology GmbH Gustav-Heinemann Ring 125 D-81739 Munich, Germany Tel: 49-89-627-144 0 Fax: 49-89-627-144-44 Germany Analog Product Sales Lochhamer Strasse 13 D-82152 Martinsried, Germany Tel: 49-89-895650-0 Fax: 49-89-895650-22 Italy Arizona Microchip Technology SRL Centro Direzionale Colleoni Palazzo Taurus 1 V. Le Colleoni 1 20041 Agrate Brianza Milan, Italy Tel: 39-039-65791-1 Fax: 39-039-6899883 **United Kingdom** Arizona Microchip Technology Ltd. 505 Eskdale Road Winnersh Triangle Wokingham Berkshire, England RG41 5TU Tel: 44 118 921 5869 Fax: 44-118 921-5820

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01/09/01